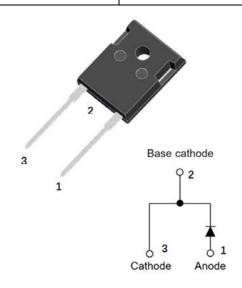




Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (135°C)}	33A
Qc	120nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-247AC

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D112020NGG3
Reverse voltage (Repetitive peak) @ T _i =25°C	V_{RRM}	٧	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	٧	1200
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	1200
Continuous forward current @ T _C =25°C			70
Continuous forward current @ T _C =135°C	I _F	А	33
Continuous forward current @ T _C =158°C			20
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	Α	210
Repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FRM}	А	100
Power Dissipation@ T _c =25°C	Б	10/	326
Power Dissipation@ T _C =110°C	P _{TOT}	W	141
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	220
Operating junction and Storage temperature range	T_j , T_stg	°C	-55 to +175





■Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =20A, T _j =25°C	1.38	1.55
			I _F =20A, T _j =175°C	1.88	-
Reverse current	I _R	μА	V _R =1200V, T _j =25°C	0.5	20
			V _R =1200V, T _j =175°C	8	-
Total capacitive charge	Q _C	nC	$V_R=800V, T_j=25^{\circ}C, Q_C=\int_0^{VR}C(V)dV$	120	-
Total capacitance	C	pF	V _R =0V, f=1MHZ	1675	-
			V _R =400V, f=1MHZ	113	-
			V _R =800V, f=1MHZ	85	-
Capacitance stored energy	Ec	μJ	V _R =800V	31	-

■Thermal Characteristics (Ta=25 °C Unless otherwise specified)

PARAMET	ER SYI	MBOL UN	І Т	VALUE
Thermal resis	ance F	R _{θJ-C} °C	w	0.46

■Characteristics (Typical)

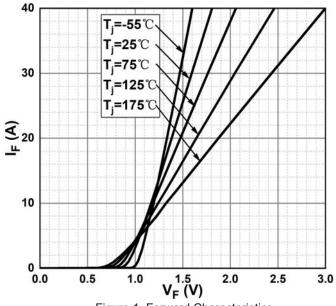


Figure 1. Forward Characteristics

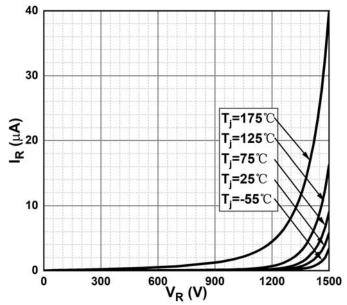
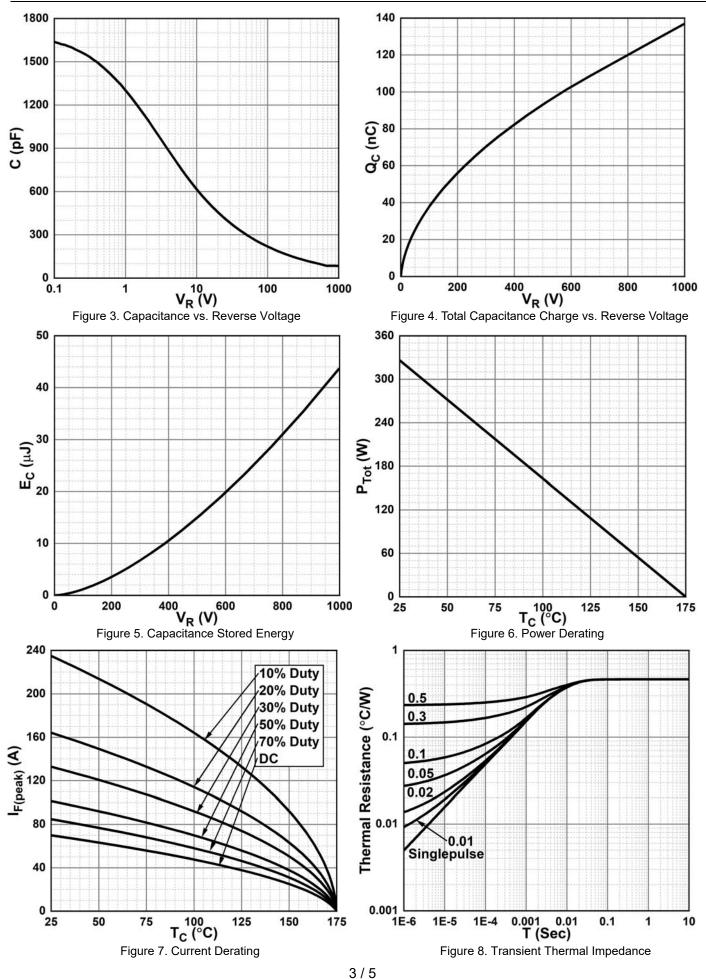


Figure 2. Reverse Characteristic



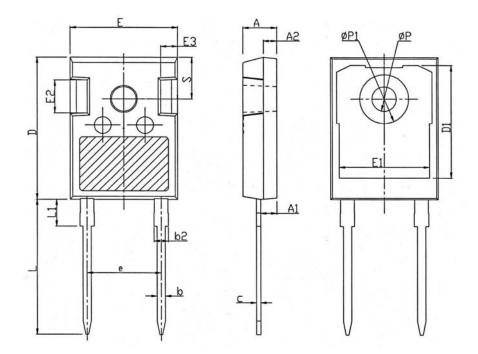








■Outline Dimensions



TO247-AC				
Dim	Min	Max		
Α	4.80	5.20		
A1	2.21	2.61		
A2	1.85	2.15		
b	1.11	1.36		
b2	1.91	2.21		
С	0.51	0.75		
D	20.70	21.30		
D1	16.25	16.85		
Е	15.50	16.10		
E1	13.00	13.60		
E2	4.80	5.20		
E3	2.30	2.70		
е	10.88BSC			
L	19.62	20.22		
L1	-	4.30		
φР	3.40	3.80		
φP1	-	7.30		
S	6.15BSC			



YJD112020NGG3



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